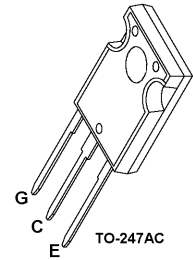
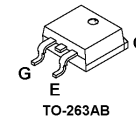
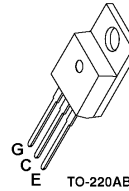
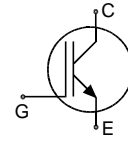


## Fast S-IGBT in NPT-technology

- 40% lower  $E_{off}$  compared to previous generation
- Short circuit withstand time – 10  $\mu$ s
- Designed for:
  - Motor controls
  - Inverter
  - SMPS
- NPT-Technology offers:
  - very tight parameter distribution
  - high ruggedness, temperature stable behaviour
  - parallel switching capability



Type	$V_{CE}$	$I_C$	$E_{off}$	$T_j$	Package	Ordering Code
SGP15N120	1200V	15A	1.5mJ	150°C	TO-220AB	Q67040-S4274
SGB15N120					TO-263AB(D2PAK)	Q67040-S4275
SGW15N120					TO-247AC	Q67040-S4276

### Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CE}$	1200	V
DC collector current	$I_C$		A
$T_C = 25^\circ\text{C}$		30	
$T_C = 100^\circ\text{C}$		15	
Pulsed collector current, $t_p$ limited by $T_{jmax}$	$I_{Cpuls}$	52	
Turn off safe operating area $V_{CE} \leq 1200\text{V}, T_j \leq 150^\circ\text{C}$	-	52	
Gate-emitter voltage	$V_{GE}$	$\pm 20$	V
Avalanche energy, single pulse $I_C = 15\text{A}, V_{CC} = 50\text{V}, R_{GE} = 25\Omega$ , start at $T_j = 25^\circ\text{C}$	$E_{AS}$	85	mJ
Short circuit withstand time <sup>1)</sup> $V_{GE} = 15\text{V}, 100\text{V} \leq V_{CC} \leq 1200\text{V}, T_j \leq 150^\circ\text{C}$	$t_{SC}$	10	$\mu$ s
Power dissipation $T_C = 25^\circ\text{C}$	$P_{tot}$	198	W
Operating junction and storage temperature	$T_j, T_{stg}$	-55...+150	°C
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

<sup>1)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

### Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
<b>Characteristic</b>				
IGBT thermal resistance, junction – case	$R_{thJC}$		0.63	K/W
Thermal resistance, junction – ambient	$R_{thJA}$	TO-220AB TO-247AC	62 40	
SMD version, device on PCB <sup>1)</sup>	$R_{thJA}$	TO-263AB(D2PAK)	40	

### Electrical Characteristic, at $T_j = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>Static Characteristic</b>						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=1000\mu A$	1200	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=15A$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	2.5 -	3.1 3.7	3.6 4.3	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=600\mu A, V_{CE}=V_{GE}$	3	4	5	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	- -	- -	200 800	$\mu A$
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=1200V, V_{GE}=0V$	-	-	100	nA
Transconductance	$g_{fs}$	$V_{CE}=20V, I_C=15A$		11	-	S
<b>Dynamic Characteristic</b>						
Input capacitance	$C_{iss}$	$V_{CE}=25V, V_{GE}=0V, f=1\text{MHz}$	-	1290	1550	pF
Output capacitance	$C_{oss}$		-	155	185	
Reverse transfer capacitance	$C_{riss}$		-	90	110	
Gate charge	$Q_{Gate}$	$V_{CC}=960V, I_C=15A, V_{GE}=15V$	-	130	175	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$	TO-220AB TO-247AC	-	7 13	-	nH
Short circuit collector current <sup>2)</sup>	$I_{C(SC)}$	$V_{GE}=15V, t_{SC}\leq 5\mu s, 100V\leq V_{CC}\leq 1200V, T_j\leq 150^\circ\text{C}$	-	145	-	A

<sup>1)</sup> Device on 50mm\*50mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70μm thick) copper area for collector connection. PCB is vertical without blown air.

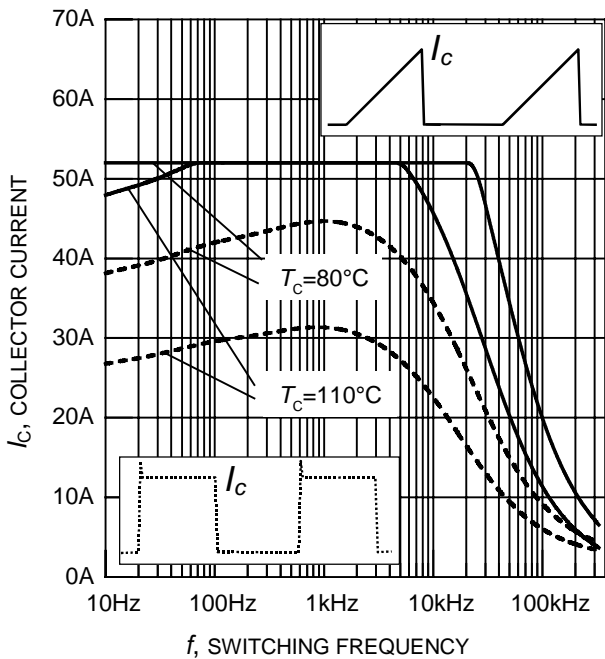
<sup>2)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

**Switching Characteristic, Inductive Load, at  $T_j=25\text{ }^\circ\text{C}$** 

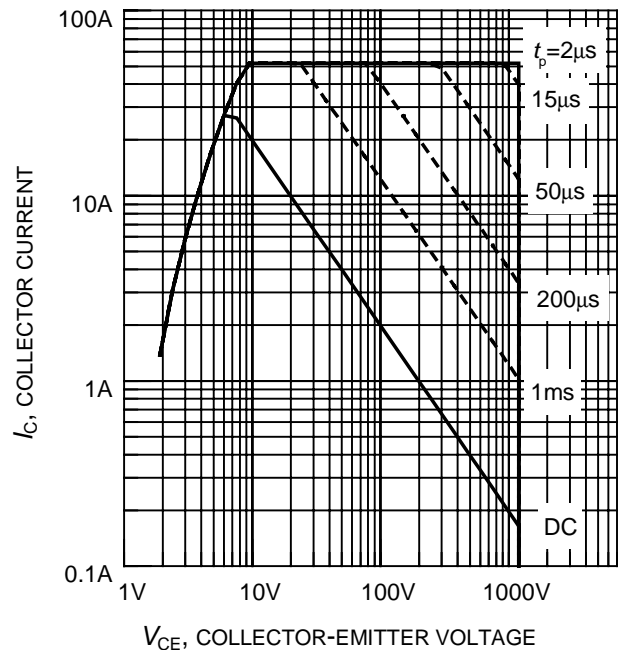
Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=25\text{ }^\circ\text{C}$ , $V_{CC}=800\text{V}$ , $I_C=15\text{A}$ , $V_{GE}=15\text{V}/0\text{V}$ , $R_G=33\Omega$ ,	-	18	24	ns
Rise time	$t_r$		-	23	30	
Turn-off delay time	$t_{d(off)}$		-	580	750	
Fall time	$t_f$		-	22	29	
Turn-on energy	$E_{on}$	Energy losses include "tail" and diode reverse recovery.	-	1.1	1.5	mJ
Turn-off energy	$E_{off}$		-	0.8	1.1	
Total switching energy	$E_{ts}$		-	1.9	2.6	

**Switching Characteristic, Inductive Load, at  $T_j=150\text{ }^\circ\text{C}$** 

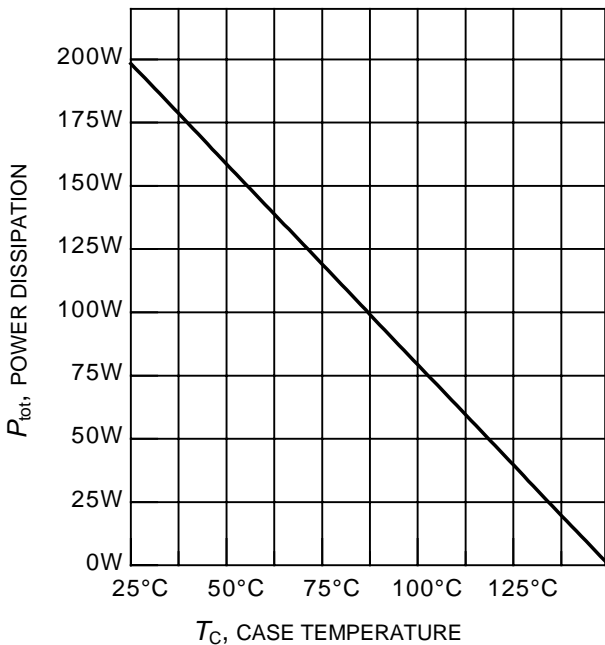
Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=150\text{ }^\circ\text{C}$ $V_{CC}=800\text{V}$ , $I_C=15\text{A}$ , $V_{GE}=15\text{V}/0\text{V}$ , $R_G=33\Omega$	-	38	46	ns
Rise time	$t_r$		-	30	36	
Turn-off delay time	$t_{d(off)}$		-	652	780	
Fall time	$t_f$		-	31	37	
Turn-on energy	$E_{on}$	Energy losses include "tail" and diode reverse recovery.	-	1.9	2.3	mJ
Turn-off energy	$E_{off}$		-	1.5	2.0	
Total switching energy	$E_{ts}$		-	3.4	4.3	



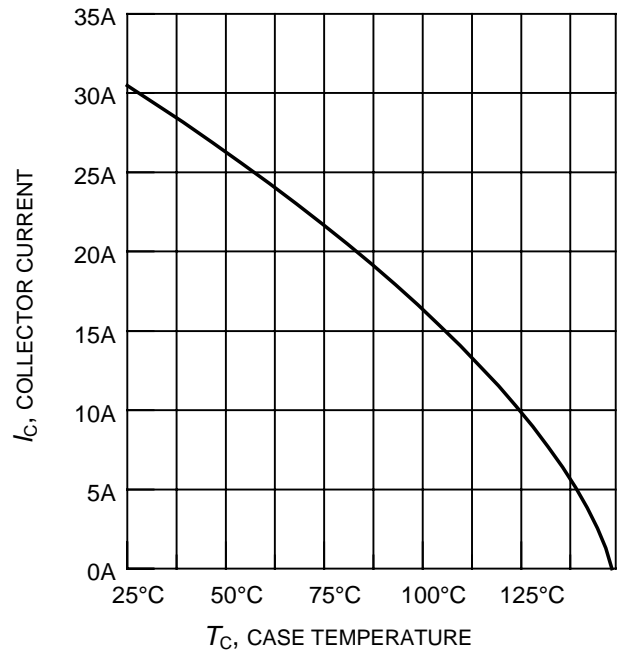
**Figure 1. Collector current as a function of switching frequency**  
 ( $T_j \leq 150^\circ\text{C}$ ,  $D = 0.5$ ,  $V_{CE} = 800\text{V}$ ,  
 $V_{GE} = +15\text{V}/0\text{V}$ ,  $R_G = 33\Omega$ )



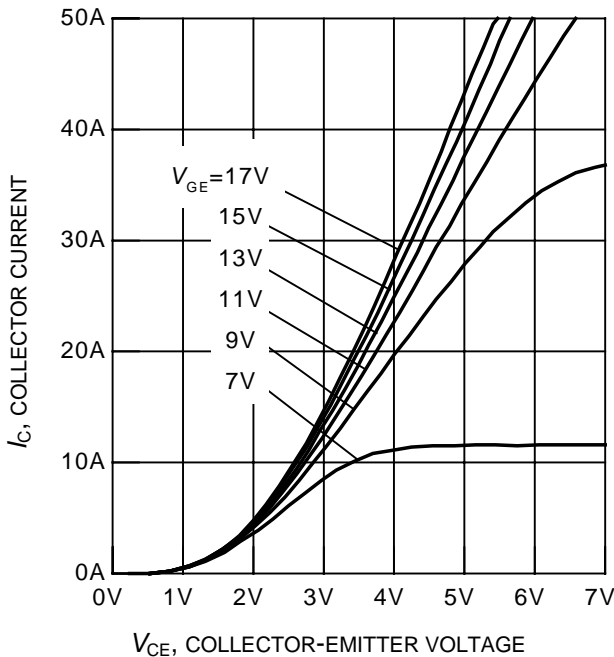
**Figure 2. Safe operating area**  
 ( $D = 0$ ,  $T_C = 25^\circ\text{C}$ ,  $T_j \leq 150^\circ\text{C}$ )



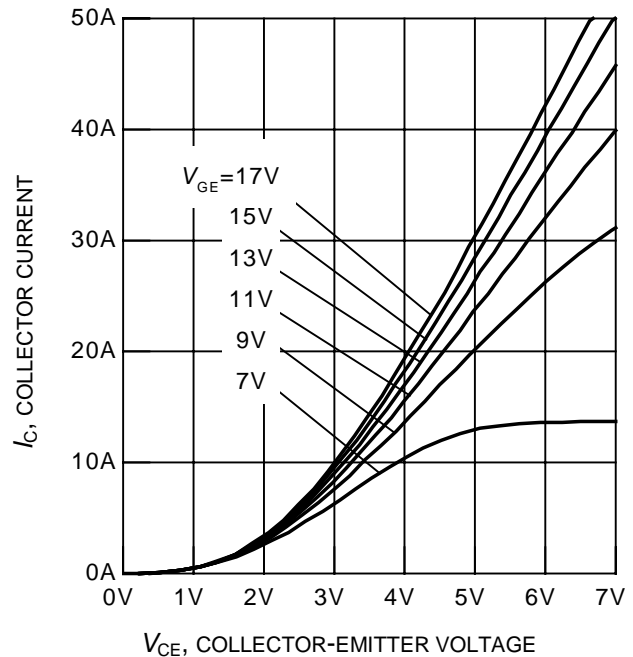
**Figure 3. Power dissipation as a function of case temperature**  
 ( $T_j \leq 150^\circ\text{C}$ )



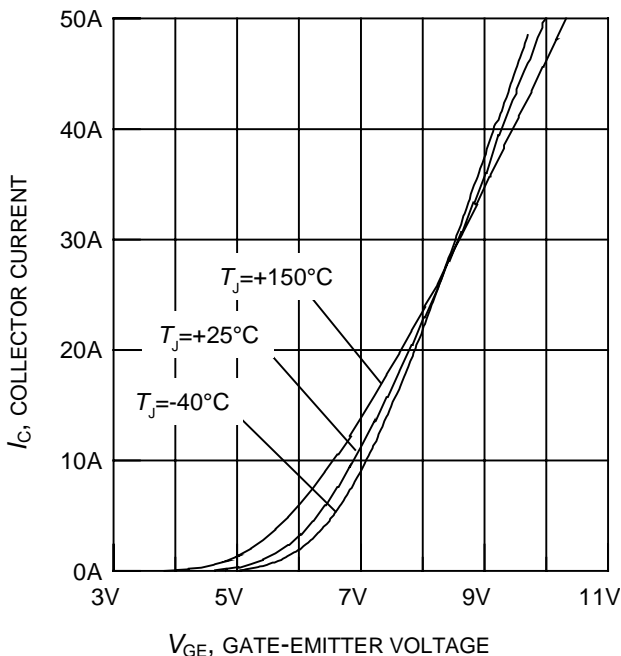
**Figure 4. Collector current as a function of case temperature**  
 ( $V_{GE} \leq 15\text{V}$ ,  $T_j \leq 150^\circ\text{C}$ )



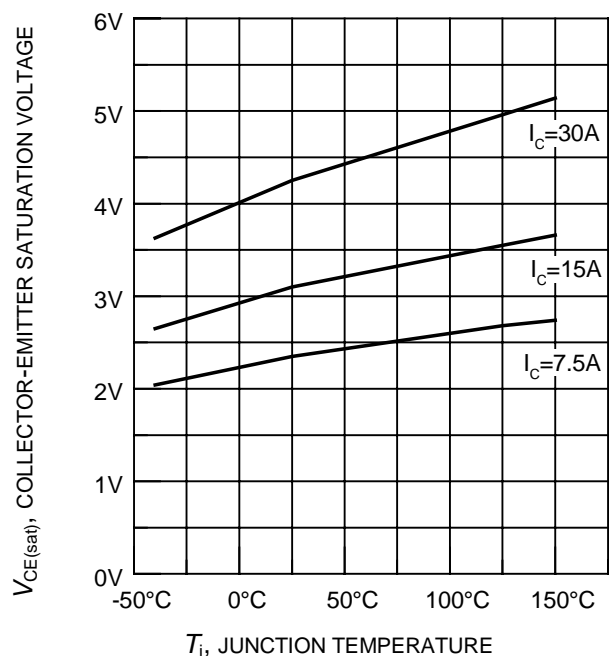
**Figure 5. Typical output characteristics**  
( $T_j = 25^\circ\text{C}$ )



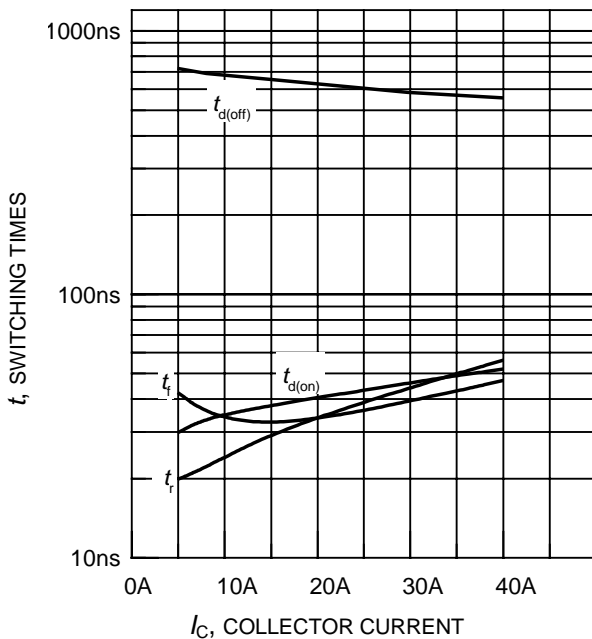
**Figure 6. Typical output characteristics**  
( $T_j = 150^\circ\text{C}$ )



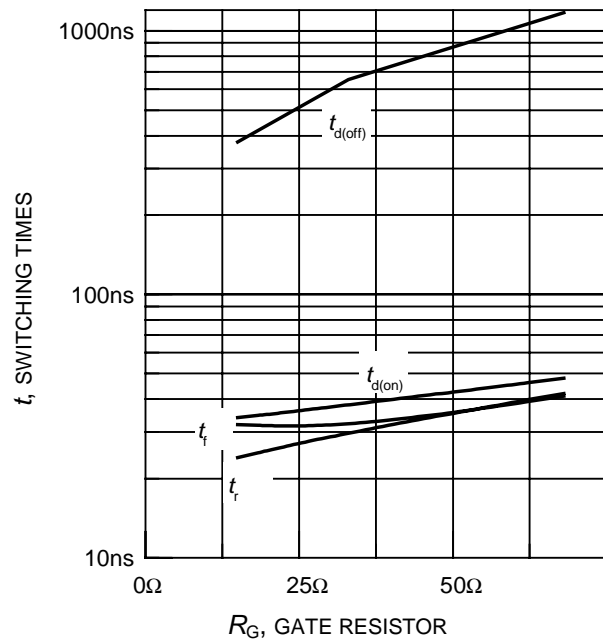
**Figure 7. Typical transfer characteristics**  
( $V_{CE} = 20\text{V}$ )



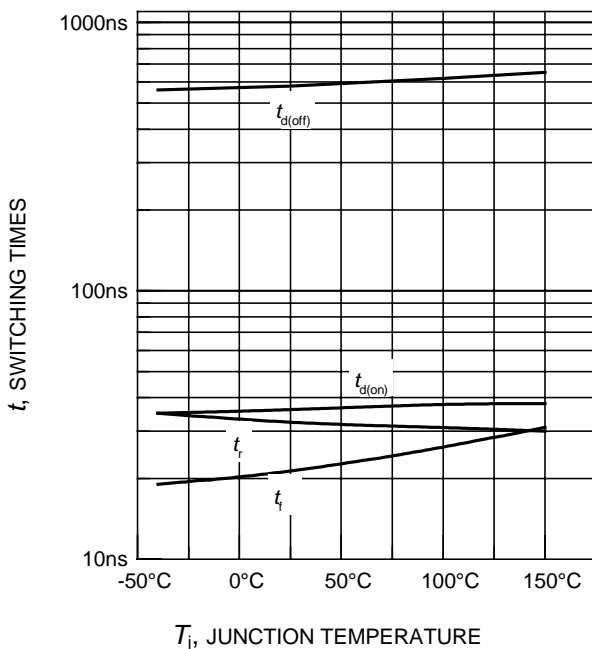
**Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature**  
( $V_{GE} = 15\text{V}$ )



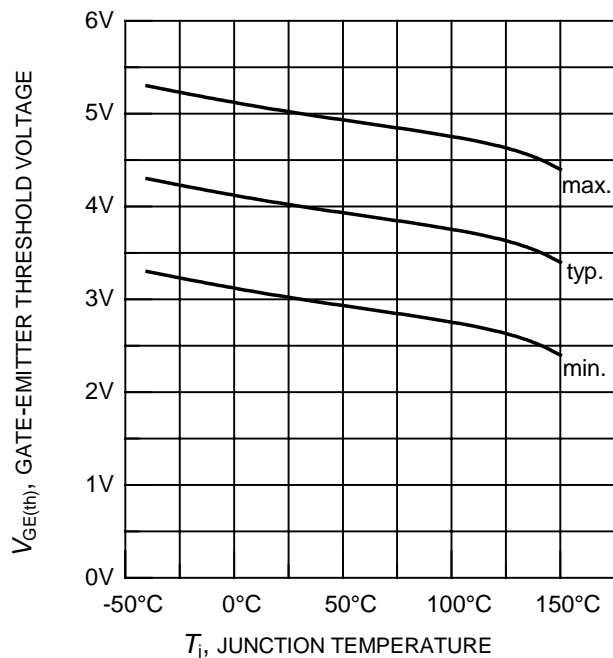
**Figure 9. Typical switching times as a function of collector current**  
 (inductive load,  $T_j = 150^\circ\text{C}$ ,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $R_G = 33\Omega$ )



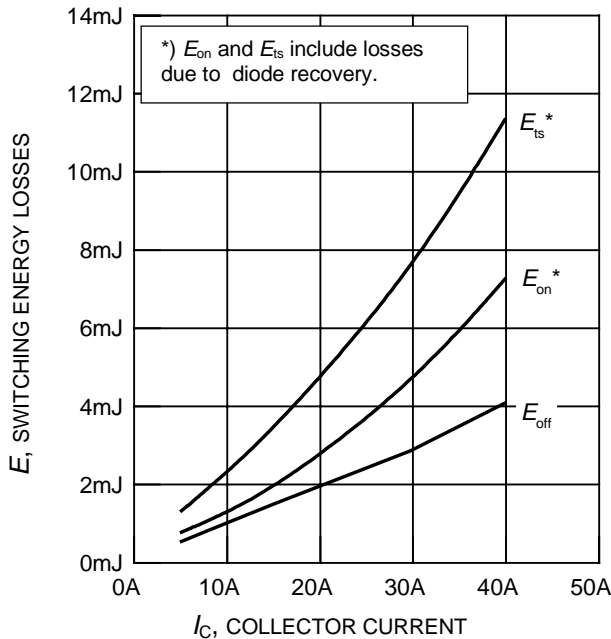
**Figure 10. Typical switching times as a function of gate resistor**  
 (inductive load,  $T_j = 150^\circ\text{C}$ ,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 15\text{A}$ )



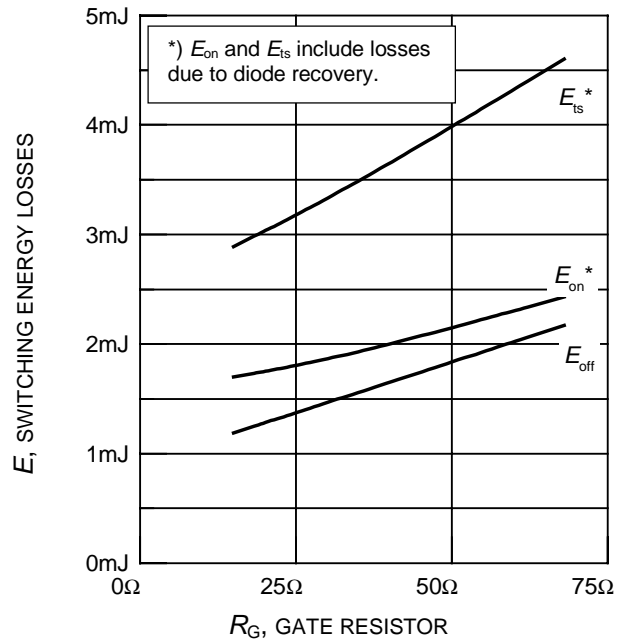
**Figure 11. Typical switching times as a function of junction temperature**  
 (inductive load,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 15\text{A}$ ,  $R_G = 33\Omega$ )



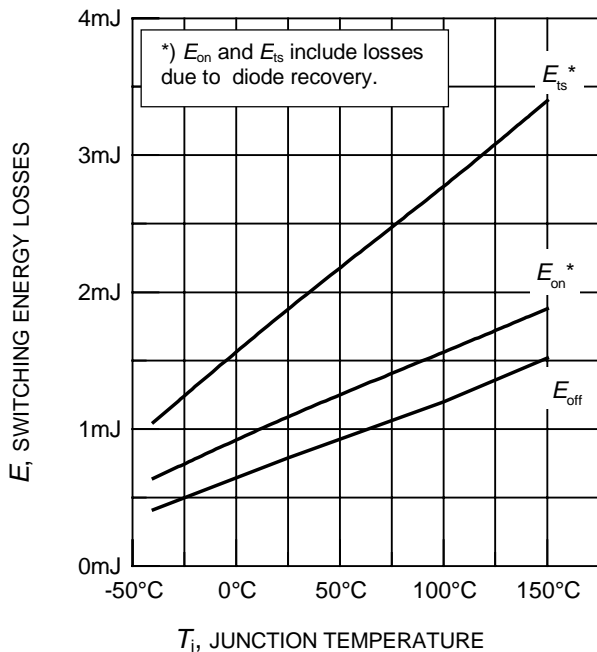
**Figure 12. Gate-emitter threshold voltage as a function of junction temperature**  
 ( $I_C = 0.3\text{mA}$ )



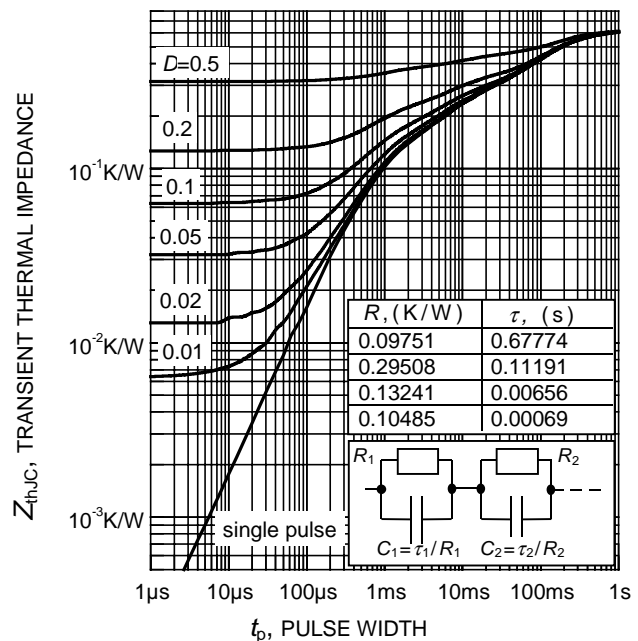
**Figure 13. Typical switching energy losses as a function of collector current**  
 (inductive load,  $T_j = 150^\circ\text{C}$ ,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $R_G = 33\Omega$ )



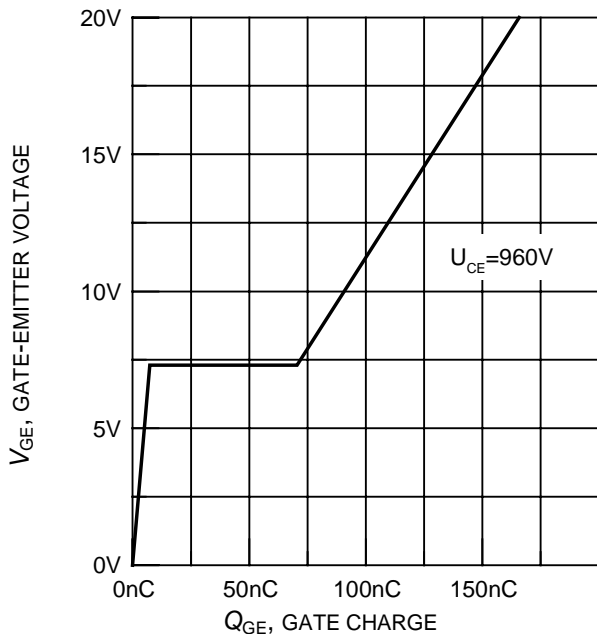
**Figure 14. Typical switching energy losses as a function of gate resistor**  
 (inductive load,  $T_j = 150^\circ\text{C}$ ,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 15\text{A}$ )



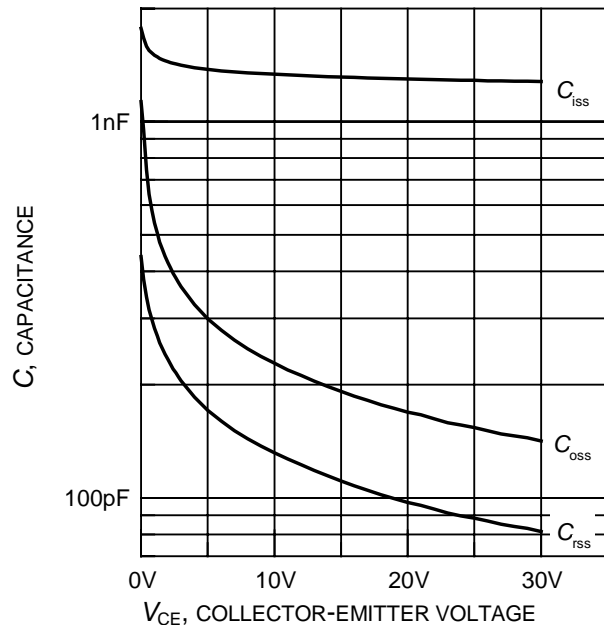
**Figure 15. Typical switching energy losses as a function of junction temperature**  
 (inductive load,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 15\text{A}$ ,  $R_G = 33\Omega$ )



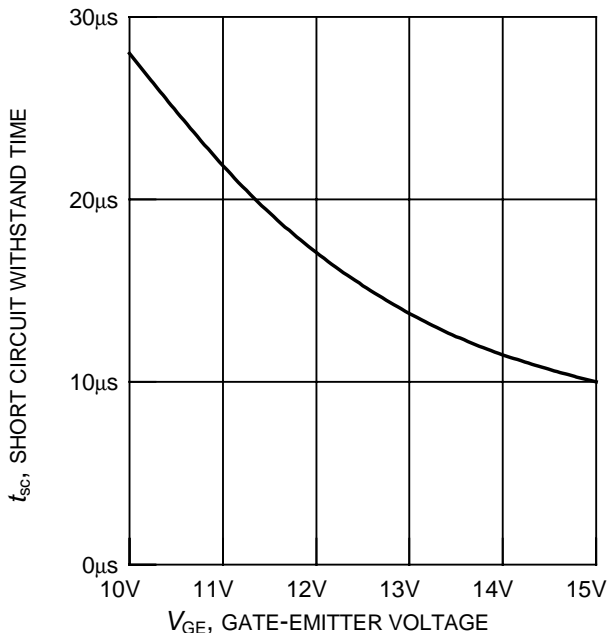
**Figure 16. IGBT transient thermal impedance as a function of pulse width**  
 ( $D = t_p / T$ )



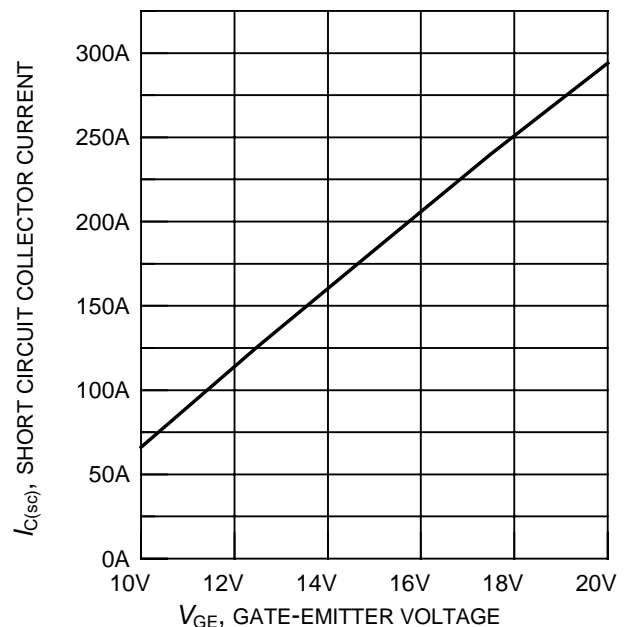
**Figure 17. Typical gate charge**  
( $I_C = 15A$ )



**Figure 18. Typical capacitance as a function of collector-emitter voltage**  
( $V_{GE} = 0V, f = 1MHz$ )



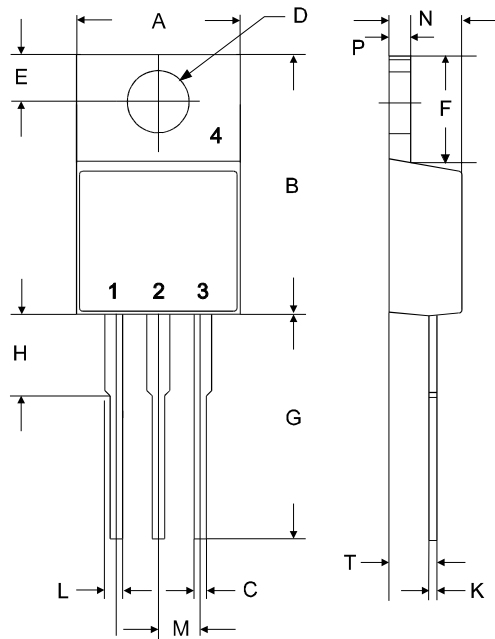
**Figure 19. Short circuit withstand time as a function of gate-emitter voltage**  
( $V_{CE} = 1200V$ , start at  $T_j = 25^\circ C$ )



**Figure 20. Typical short circuit collector current as a function of gate-emitter voltage**  
( $100V \leq V_{CE} \leq 1200V, T_C = 25^\circ C, T_j \leq 150^\circ C$ )

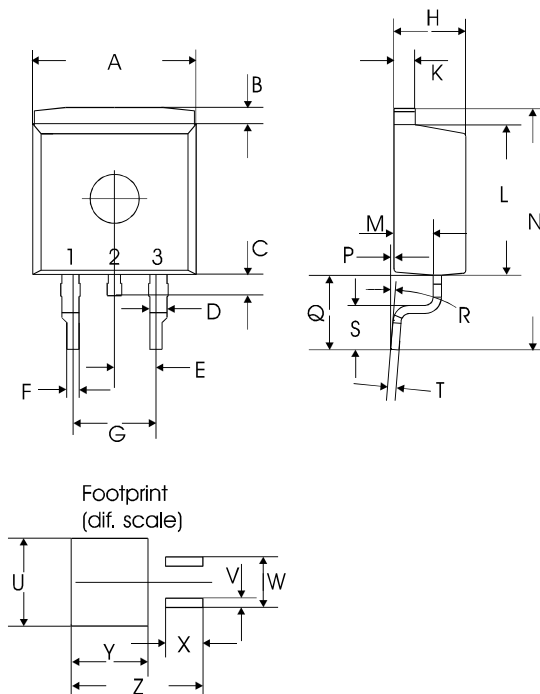


TO-220AB

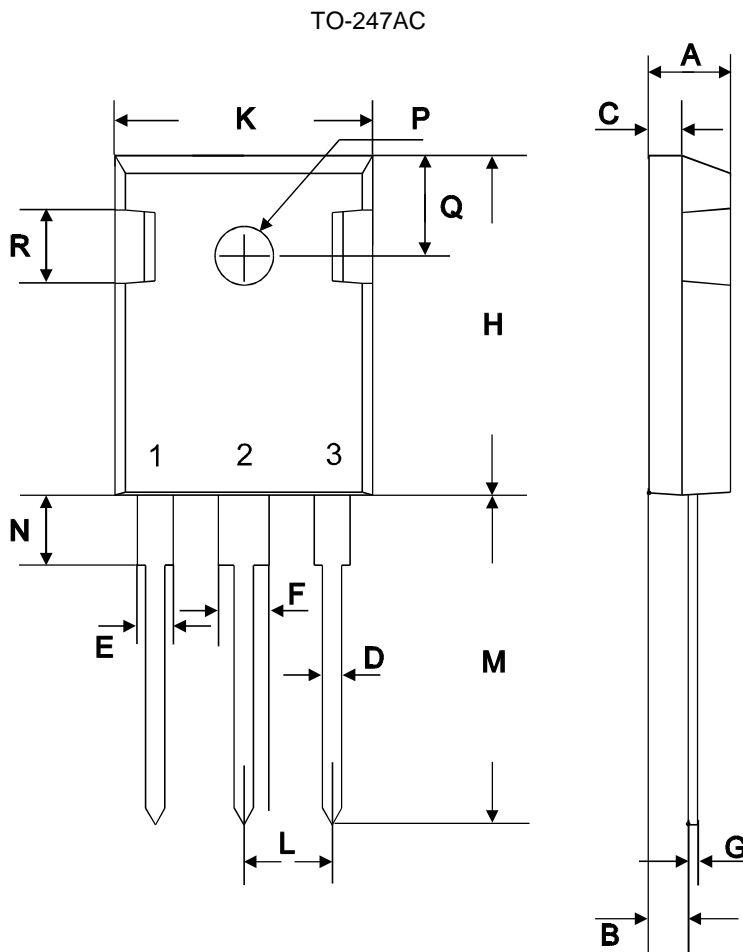


symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	9.70	10.30	0.3819	0.4055
B	14.88	15.95	0.5858	0.6280
C	0.65	0.86	0.0256	0.0339
D	3.55	3.89	0.1398	0.1531
E	2.60	3.00	0.1024	0.1181
F	6.00	6.80	0.2362	0.2677
G	13.00	14.00	0.5118	0.5512
H	4.35	4.75	0.1713	0.1870
K	0.38	0.65	0.0150	0.0256
L	0.95	1.32	0.0374	0.0520
M	2.54 typ.		0.1 typ.	
N	4.30	4.50	0.1693	0.1772
P	1.17	1.40	0.0461	0.0551
T	2.30	2.72	0.0906	0.1071

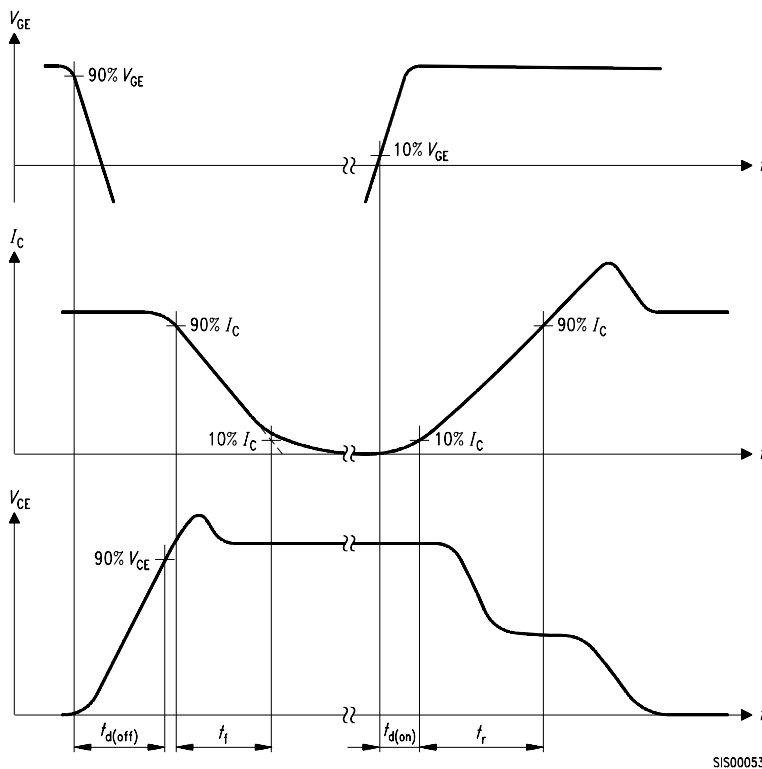
TO-263AB (D<sup>2</sup>Pak)



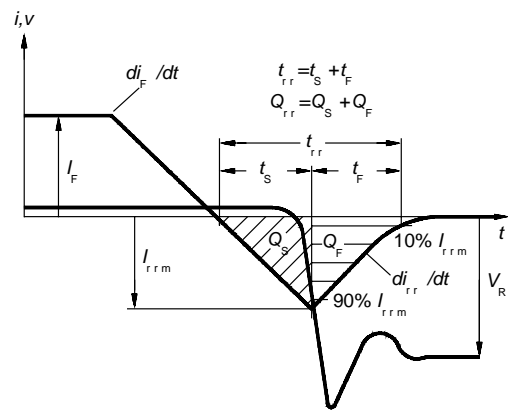
symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	9.80	10.20	0.3858	0.4016
B	0.70	1.30	0.0276	0.0512
C	1.00	1.60	0.0394	0.0630
D	1.03	1.07	0.0406	0.0421
E	2.54 typ.		0.1 typ.	
F	0.65	0.85	0.0256	0.0335
G	5.08 typ.		0.2 typ.	
H	4.30	4.50	0.1693	0.1772
K	1.17	1.37	0.0461	0.0539
L	9.05	9.45	0.3563	0.3720
M	2.30	2.50	0.0906	0.0984
N	15 typ.		0.5906 typ.	
P	0.00	0.20	0.0000	0.0079
Q	4.20	5.20	0.1654	0.2047
R	8° max		8° max	
S	2.40	3.00	0.0945	0.1181
T	0.40	0.60	0.0157	0.0236
U	10.80		0.4252	
V	1.15		0.0453	
W	6.23		0.2453	
X	4.60		0.1811	
Y	9.40		0.3701	
Z	16.15		0.6358	



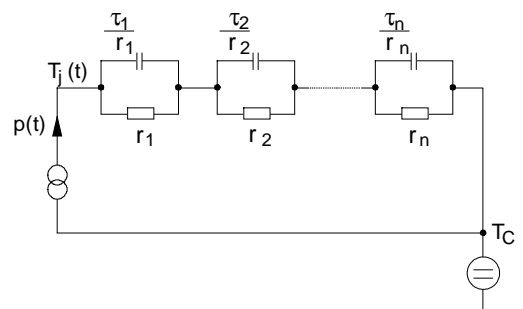
symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	4.78	5.28	0.1882	0.2079
B	2.29	2.51	0.0902	0.0988
C	1.78	2.29	0.0701	0.0902
D	1.09	1.32	0.0429	0.0520
E	1.73	2.06	0.0681	0.0811
F	2.67	3.18	0.1051	0.1252
G	0.76 max		0.0299 max	
H	20.80	21.16	0.8189	0.8331
K	15.65	16.15	0.6161	0.6358
L	5.21	5.72	0.2051	0.2252
M	19.81	20.68	0.7799	0.8142
N	3.560	4.930	0.1402	0.1941
∅P	3.61		0.1421	
Q	6.12	6.22	0.2409	0.2449



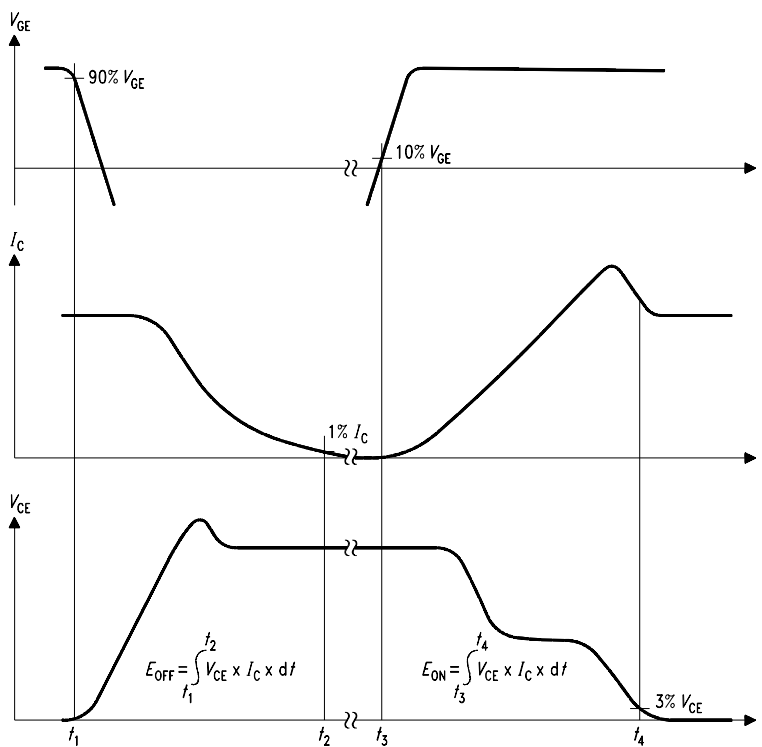
**Figure A. Definition of switching times**



**Figure C. Definition of diodes switching characteristics**



**Figure D. Thermal equivalent circuit**



**Figure B. Definition of switching losses**

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